

20V N-Channel MOSFET



SOP-8

Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gate
- 5, 6, 7, 8. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
	30 @ V _{GS} = 4.5V	4.5	
20	40 @ V _{GS} = 2.5V	3.5	
	200 @ V _{GS} = 1.8V	2.0	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

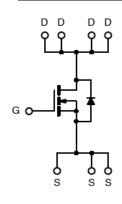
Application

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM4426CS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current		I _D	8	Α	
Pulsed Drain Current		I _{DM}	30	Α	
Continuous Source Current (Diode Conc	luction) ^{a,b}	Is	2.2	Α	
	Ta = 25°C	P _D	2.5	W	
Maximum Power Dissipation	Ta = 75°C		1.3		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance Junction to Foot	$R\Theta_{JF}$	25	°C/W	
Thermal Resistance Junction to Ambient	RO _{JA}	52.5	°C/W	

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.

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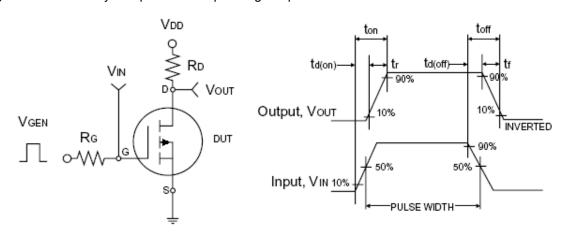
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Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6			V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
	$V_{GS} = 4.5V, I_D = 4.5A$			20	30	
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3.5A$	R _{DS(ON)}		28	40	mΩ
	$V_{GS} = 1.8V, I_D = 2.0A$			80	200	
Forward Transconductance	$V_{DS} = 10V, I_D = 6A$	g _{fs}		30		S
Diode Forward Voltage	I _S = 1.7A, V _{GS} = 0V	V_{SD}		0.7	1.2	V
Dynamic ^b						
Total Gate Charge	V _{DS} = 10V, I _D = 6A,	Q_g		4.86		
Gate-Source Charge	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$	Q_gs		0.92		nC
Gate-Drain Charge	V _{GS} = 4.5 V	Q_gd		1.4		
Input Capacitance	\\ - 0\\ \\ - 0\\	C_{iss}		562		
Output Capacitance	$V_{DS} = 8V, V_{GS} = 0V,$	C_{oss}		106		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		75		
Switching ^c						
Turn-On Delay Time	$V_{DD} = 10V, R_L = 10Ω,$ $I_D = 1A, V_{GEN} = 4.5V,$	t _{d(on)}		15		
Turn-On Rise Time		t _r		65		20
Turn-Off Delay Time		t _{d(off)}		28.4		nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		12		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

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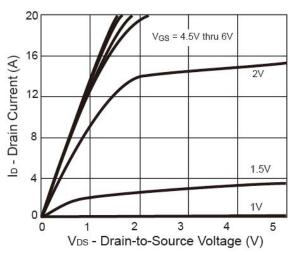


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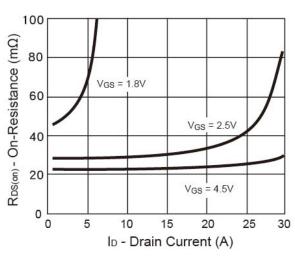


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

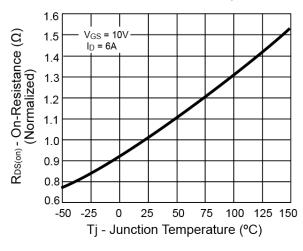




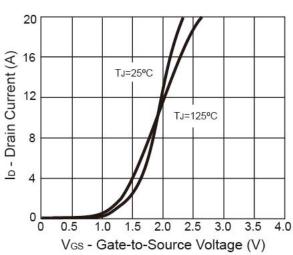
On-Resistance vs. Drain Current



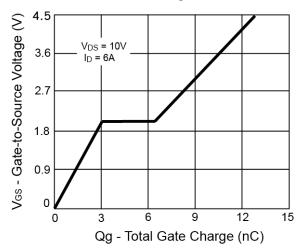
On-Resistance vs. Junction Temperature



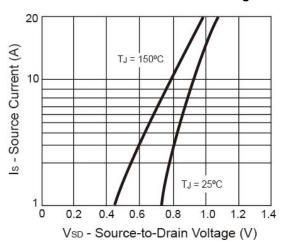
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



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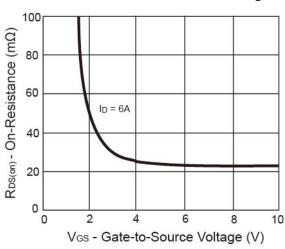


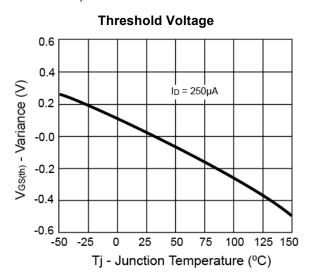




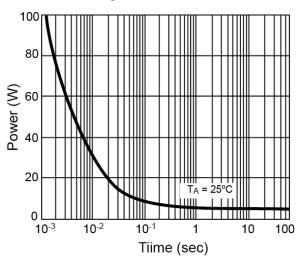
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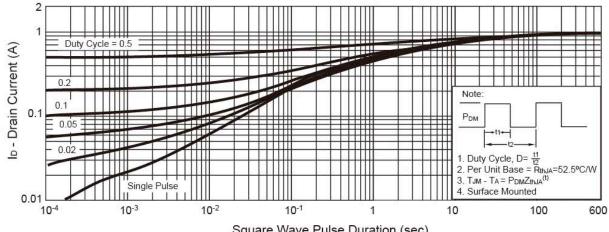




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

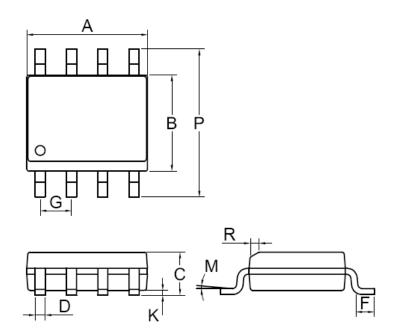
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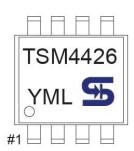


SOP-8 Mechanical Drawing



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code

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TSM4426 20V N-Channel MOSFET

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